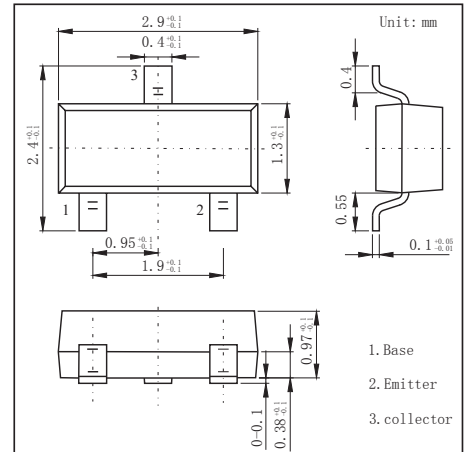


SOT-23 Plastic-Encapsulate Transistors
FEATURES

- High voltage and high current
- High hFE: hFE = 70~400
- Low noise: NF = 1dB (typ.), 10dB (max)
- Complementary to 2SC2712
- PNP Transistors

MECHANICAL DATA

- Case style: SOT-23 -3molded plastic
- Mounting position: any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-50	V
Collector - Emitter Voltage	V _{CE0}	-50	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _c	-150	mA
Base Current	I _B	-30	
Collector Power Dissipation	P _c	150	mW
Junction Temperature	T _J	125	°C
Storage Temperature range	T _{stg}	-55 to 125	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E = 0	-50			V
Collector- emitter breakdown voltage	V _{CE0}	I _c = -1 mA, I _B = 0	-50			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _c = 0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -50 V, I _E = 0			-100	nA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V, I _c = 0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c = -100 mA, I _B = -10mA			-0.3	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c = -100 mA, I _B = -10mA			-1.2	
DC current gain	h _{FE}	V _{CE} = -6V, I _c = -2mA	70		400	
Noise figure	NF	V _{CE} = -6 V, I _c = -0.1 mA, f = 1 kHz R _g = 10 kΩ,			10	dB
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz			7	pF
Transition frequency	f _t	V _{CE} = -10V, I _c = -1mA	80			MHz

RATINGS AND CHARACTERISTIC CURVES

